

STD830CP20

Complementary transistor pair in a single package

Preliminary data

Features

- Low V_{CE(sat)}
- Simplified circuit design
- Reduced component count
- Low spread of dynamic parameters

Applications

■ Compact fluorescent lamp (CFL) 110 V mains

Description

The STD830CP20 is a hybrid complementary pair of power bipolar transistors manufactured by using the high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

The STD830CP20 is housed in dual island DIP-8 package with separated terminals for higher assembly flexibility, specifically recommended to be used in a new solution for compact fluorescent lamp (CFL).

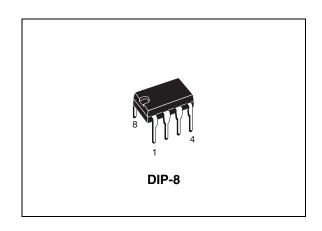


Figure 1. Internal schematic diagram

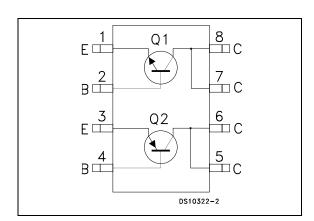


Table 1. Device summary

Order code	Marking	Package	Packing
STD830CP20	D830CP20	DIP-8	Tube

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Electrical ratings STD830CP20

1 Electrical ratings

Table 2. Absolute maximum ratings

Compleal	Paramatan.	Value		l l m i h
Symbol	Parameter	NPN	PNP	Unit
V _{CBO}	Collector-base voltage (I _E = 0)		300	V
V _{CEO}	Collector-emitter voltage (I _B = 0) 200		00	V
V _{EBO}	Emitter-base voltage ($I_C = 0$, $I_b = 1.5 \text{ A}$, $t_p < 10 \text{ ms}$)	V _{(BR)EBO}		V
I _C	Collector current		3	
I _{CM}	Collector peak current (t _P < 5 ms)	6		Α
I _B	Base current	1.5		Α
I _{BM}	Base peak current (t _P < 1 ms)	3		Α
P _{tot}	Total dissipation at T _{amb} = 25 °C single transistor	TBD		W
P _{tot}	P _{tot} Total dissipation at T _{amb} = 25 °C both transistors		TBD	
T _{stg}	T _{stg} Storage temperature		-65 to 150	
T _J Max. operating junction temperature		150		°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-ambient (Single transistor)	TBD	°C/W
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-ambient (Both transistors)	TBD	°C/W

^{1.} When mounted on 1 inch square pad of 2 oz. copper, $t \le 10$ sec.

Note: For PNP types voltage and current values are negative

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	For NPN: V _{CE} = 400 V V _{CE} = 400 V For PNP: V _{CE} = 300 V V _{CF} = 300 V T _C = 125°C			0.1 0.5 0.1 0.5	mA mA mA
$V_{(BR)EBO}$ Emitter-base breakdown voltage ($I_C = 0$)		I _E = 10 mA For NPN: For PNP:	9		18 12	V V
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C = 5 mA	200			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_C = 0.5 \text{ A}$ $I_B = 0.05 \text{ A}$ $I_C = 0.7 \text{ A}$ $I_B = 0.1 \text{ A}$			400 400	mV mV
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	$I_C = 0.5 \text{ A}$ $I_B = 0.1 \text{ A}$ $I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$			1 1.1	V V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} & _{C} = 10 \text{ mA} & V_{CE} = 5 \text{ V} \\ & _{C} = 0.75 \text{ A} & V_{CE} = 5 \text{ V} \\ & _{C} = 2 \text{ A} & V_{CE} = 5 \text{ V} \end{split}$	22		36	
t _r t _s	Resistive load Rise time Storage time Fall time	$I_C = 0.7 \text{ A}$ $V_{CC} = 150 \text{ V}$ $I_{B1} = 0.14 \text{ A}$ $I_{B2} = -0.14 \text{ A}$ $I_p = 30 \mu\text{s}$		80 1.2 80		ns µs ns
t _s	Inductive load Storage time Fall time	$\begin{split} I_{C} &= 1 \text{ A} & I_{B1} = 0.1 \text{ A} \\ V_{BE(off)} &= -5 \text{ V} & R_{BB} = 0 \\ V_{clamp} &= 150 \text{ V} & L = 1 \text{ mH} \end{split}$		120 50		ns ns

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1.5 %

Note: For PNP types voltage and current values are negative

3 Package mechanical data

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Table 5. DIP-8 mechanical data

Di		mm.	
Dim.	Min	Тур.	Max.
А			4.80
A1	0.50		
A2	3.10		3.50
A3	1.40		1.60
b	0.38		0.55
b1	0.38		0.51
b2	1.47		1.57
b3	0.89		1.09
С	0.21		0.35
c1	0.20		0.30
D	9.10		9.30
D1	0.13		
E	7.62		8.25
E1	6.25		6.45
е		2.54	
eA		7.62	
eB	7.62		10.90
eC	0		1.52
L	2.92		3.81

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Figure 2. Drawing dimension DIP-8

Revision history STD830CP20

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
26-May-2009	1	Initial release.

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